Columnar defects and vortex fluctuations in layered superconductors

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We investigate fluctuations of Josephson-coupled pancake vortices in layered superconductors in the presence of columnar defects. We study the thermodynamics of a single pancake stack pinned by columnar defects and obtain the temperature dependence of localization length, pinning energy and critical current. We study the creep regime and compute the crossover current between line-like creep and pancake-like creep motion. We find that columnar defects effectively increase interlayer Josephson coupling by suppressing thermal fluctuations of pancakes. This leads to an upward shift in the decoupling line most pronounced around the matching field.

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The question of the effective dimensionality of the vortex structure in highly anisotropic high-T_c superconductors is the subject of intense experimental and theoretical interest. It was predicted that thermal fluctuations of vortex positions produce strong relative phase fluctuations in adjacent layers and that the phase coherence along the c-axis is destroyed above the decoupling line (DL) in the $H-T$ plane [1]. Above this line an additional transverse field is not screened by Josephson currents and completely penetrates the sample. Several experiments were interpreted [2] as a manifestation of decoupling effects.

In this Letter we focus on the influence of columnar defects produced by heavy ion irradiation on the vortex decoupling and the resulting effective dimensionality of the vortex structure. The interest in this question is motivated not only by the technological importance of highly anisotropic compounds such as $Bi_2Sr_2CaCu_2O_x$ (BSCCO), but also by the expected rich variety of nontrivial dynamic and static properties arising from the interplay between the continuous linear geometry of heavy ion tracks and the discrete pancake-like character of the vortex structure.

An important question is whether columnar defects can be especially efficient to pin 2D pancakes which are nearly independent in each layers. Early experiments [3] of irradiation of BSCCO failed to show unidirectional pinning along the columns thus suggesting that the linear nature of columnar defects may not be efficient for highly anisotropic materials. However subsequent experiments revealed [4–6] that the *relative* enhancement of critical current (by several orders of magnitude) and the upward shift of the technologically useful irreversibility region, was even *greater* for highly anisotropic material such as BSCCO than for the less anisotropic YBCO.

We demonstrate that the observed enhanced pinning of pancakes can be explained in terms of the *recoupling* of the layers by the columnar defects. We show that columnar defects effectively increase the interlayer Josephson coupling by suppressing thermal fluctuations of pancakes positions. This leads to an upward shift in the decoupling line, the maximal shift being expected around the matching field. We also investigate in detail pinning regimes of a single pancake stack on a single column and on the system of columns.

The theory of vortex pinning by columnar defects in anisotropic 3D superconductors was developed in [8]. Mapping vortex lines onto the imaginary-time quantum mechanics of 2D bosons subject to static disorder leads to the prediction of a novel low temperature "Bose glass" phase with vortices localized near columnar pins, an infinite tilt modulus and zero linear resistivity. The Bose glass transition line $B_{BG}(T)$ is shifted to higher temperatures as compared to the melting line $B_m(T)$ of the clean lattice. The existence of the Bose glass phase is supported by several experiments [7,6]. A new feature of highly anisotropic superconductors is the discrete nature of vortices. The physics of the system is governed by three characteristic lengths: the vortex spacing $a = (\Phi_0/B)^{1/2}$, the distance between defects d and the Josephson length γs. Here B is the magnetic induction, Φ_0 is the flux quantum, s the interlayer spacing and γ is the anisotropy parameter. The Josephson length defines the crossover field $B_{cr} = \Phi_0/(\gamma s)^2$ above which the interplane interaction energy of pancakes exceeds the interlayer coupling. The discreteness changes the depinning temperature, localization length, binding energy, and critical current. We calculate these parameters using a discrete-time generalization of the mapping onto quantum mechanics. We show that at low temperature and moderate fields the system crosses over from pancake to line-like behaviour. We study this crossover

at short scales in thermodynamic quantities and in transport properties as a function of the current. At elevated temperatures and fields the layered nature of the superconductor is essential and leads to a new phase, the "decoupled Bose glass", where the phase coherence along the c-axis is lost but pancakes are aligned by columns and therefore the system exhibits infinite tilt stiffness.

The statistical mechanics of a single stack of pancakes near a columnar defect is determined by the partition function:

$$Z_N(\mathbf{r}_0,\mathbf{r}_N) = \int\limits_{r_n>b_0} \prod_{0<n<N} \frac{\epsilon_1 d\mathbf{r}_n}{2\pi s T} \exp\left(-\frac{1}{T}\sum_{n=1}^{N}\left[\frac{\epsilon_1}{2s}(\mathbf{r}_n-\mathbf{r}_{n-1})^2+V(\mathbf{r}_n)\right]\right) \quad (1)$$

depending on the positions of the start and end points $\mathbf{r}_0, \mathbf{r}_N$ [13]. The Josephson coupling binds the pancakes in the neighboring layers by a spring-like interaction with the elastic constant $\epsilon_1 = (\epsilon_0/\gamma^2)\ln(\gamma s/r_{cut})$ where ϵ_1 is the elastic tension in the continuous limit, $\epsilon_0 = \Phi_0^2/(4\pi\lambda)^2$, λ is the London penetration depth for the currents flowing along ab planes and r_{cut} being the cut off radius of order of b_0 if $r_n, r_{n-1} \lesssim 2b_0$ and of order of $|r_n - r_{n-1}|$ otherwise. We assume $\gamma < \lambda/s$, and therefore neglect the magnetic coupling as compared to the Josephson one. We model columnar defects as cylinders of normal material of the radius b_0. The pancakes interaction with the columnar defect is given by an attractive pinning potential $V(r)$, which at $r - b_0 \gg \xi$ can be found from the London equations [10],

$$V(r) = s\epsilon_0 \ln\left(1 - b_0^2/r^2\right) \quad (2)$$

The maximum pinning potential per unit length is $U_0 \approx \epsilon_0\left(\ln(b_0/\xi) + 0.38\right)$.

Using the standard transfer matrix method one finds that in the large-N limit $Z_N(\mathbf{r},\mathbf{r}')$ takes the form:

$$Z_N(\mathbf{r},\mathbf{r}') = \exp(-E_0 sN/T - V(\mathbf{r}')/T)\phi_0(\mathbf{r})\phi_0(\mathbf{r}') \quad (3)$$

where E_0 (the binding energy per unit length) and $\phi_0(\mathbf{r})$ are the ground-state energy and the ground state wave function of the discrete analogue of a 2D "Shrödinger equation":

$$\exp(-E_0 s/T)\phi_0(\mathbf{r}) = \int \frac{\epsilon_1 d\mathbf{r}'}{2\pi s T}\exp\left(-\frac{\epsilon_1(\mathbf{r}-\mathbf{r}')^2}{2sT} - \frac{V(\mathbf{r}')}{T}\right)\phi_0(\mathbf{r}'). \quad (4)$$

Taking the limit $s \to 0$ recovers the usual quantum mechanical representation of vortex line. The probability of finding a pancake at point $\mathbf{r}$ near columnar defect is: $P(\mathbf{r}) = \exp(-V(\mathbf{r})/T)\phi_0^2(\mathbf{r})$

Localization effects are governed by the effective potential $U_{eff}(\mathbf{r}) = -(T/s)\left(\exp[-V(\mathbf{r})/T] - 1\right)$ which is characterized by the large dip in the close vicinity of the column and has a $1/r^2$ tail far from the defect. The small distance dip dominates at low temperatures while the large distance tail becomes important at high temperatures (the exact criterion will be specified below). At low temperatures the potential is effectively short-ranged and can be approximated by a delta-function $U_{eff}(\mathbf{r}) \approx -W\delta(\mathbf{r})$ with $W = (2\pi T/s)\int_{r>b_0} r dr(\exp[-V(r)/T] - 1)$. The main contribution to W at low temperatures comes from short distances and can be estimated as $(2\pi T b_0 r_0/s)\exp(sU_0/T)$, with the length r_0 being dependent on the detailed mechanism of the pancake nucleation at the column boundary. Approximating the pancake potential at distances $0 < r - b_0 \lesssim \xi$ by $V(r) \approx sU_0 + (s\epsilon_0/2)\ln(1 + (r-b_0)^2/\xi^2)$ we obtain $r_0 \approx \xi(T/s\epsilon_0)^{1/2}$. Within the delta-function approximation Eq. (5) can be solved exactly [11] giving the ground state energy as:

$$E_0 = (T/s)\ln\left\{1 - \exp\left(-2\pi T^2/(\epsilon_1 W)\right)\right\}. \quad (5)$$

The distribution function is then $P(\mathbf{r}) = \phi_0^2(\mathbf{r}) + (sW/T)\,\phi_0^2(0)\delta(\mathbf{r})$, i.e., it consists of the delta-peak centered at the defect having the weight $1 - \exp(sE_0/T)$ and the smooth part with the weight $\exp(sE_0/T)$. A similar structure for $P(\mathbf{r})$ has been observed in numerical simulations [13] . We define the depinning temperature T^* by the condition that at $T > T^*$ the probability to find a pancake outside the column becomes higher than the probability to find it inside the defect. Matching probabilities of finding pancake inside- and outside the defect gives rise to the self-consistent equation

$$T^* = sU_0/\ln\left(\frac{sT^*}{b_0 r_0 \epsilon_1}\right), \quad (6)$$

where the quantities U_0 and ϵ_1 are taken at $T = T^*$. Eq. (6) is valid provided $\xi_l(T^*) \gg b_0$, this is equivalent to the condition $\gamma s \gg b_0$ and defines a range of parameters corresponding to the "pancake" regime of depinning as opposed to the "elastic string" regime described in Ref. [8]. Above T^* the localization parameters obey the "exponent-in-exponent" temperature dependencies, in particular, for the localization length ξ_l, $\xi_l^2 = \int d^2\mathbf{r}\,\mathbf{r}^2\phi_0^2(\mathbf{r})$, one has

$$\xi_l^2 \approx \frac{sT}{3\epsilon_1}\exp\left[\frac{sT\exp(-sU_0/T)}{\epsilon_1 b_0 r_0}\right]. \quad (7)$$

Evaluating the parameter W with the potential from (2) one finds that the $1/r^2$ tail gives rise to a logarithmic divergence at large distances which has to be cut off at ξ_l. Finally one arrives at $W \approx \frac{2\pi}{s}Tb_0 r_0 \exp\left(\frac{sU_0}{T}\right) + \pi b_0^2\epsilon_0 \ln\frac{\xi_l^2 T}{s\epsilon_0 b_0^2}$, where the first term is due to the short distances contribution. Substituting the expression for ξ_l from Eq. (7) into the last equation we can see that the tail region dominates above the typical temperature

$T^{**} = 2sU_0/\ln\left(s^2U_0/b_0^2\epsilon_1\right) > T^*$. Numerical estimate for BSCCO with $\lambda_0 = 1800\mathring{A}$, $\gamma = 200$ $b_0 = 100\mathring{A}$ gives $T^* \approx 69$ K, $T^{**} \approx 73$ K.

At temperatures significantly larger than T^{**} discreteness is not important any more, Eq.(5) reduces to the Shrödinger equation, and the localization parameters coincides with those for the elastic string [11,14]

$$\xi_l^2 = \gamma s b_0 \exp\left(\frac{T}{T_{\rm str}}\right);\ E_0 = \frac{T^2}{T_{\rm str} b_0}\exp\left(-\frac{T}{T_{\rm str}}\right). \quad (8)$$

with $T_{\rm str} = \sqrt{2\epsilon_1\epsilon_0}b_0/\pi$. The single-column regim breaks down at temperature T_{dl} where the localization length ξ_l matches the spacing between the columns, $\xi(T_{dl}) = d$.

Next we discuss transport of the pancake vortices in the presence of columnar defects at low temperatures and fields ($B < B_\phi = \Phi_0/d^2 < B_{cr}$) below critical current. The pancake motion in this region is controlled by the liberation of a single stack of pancakes from the localized state near a columnar defect. The energy cost to liberate a segment of N pancakes is:

$$\Delta E_N = \sum_{n=1}^{N}\left(\frac{\epsilon_1}{2s}(r_n - r_{n+1})^2 + sU_0 + V(r_n)\right) - \frac{\Phi_0}{c}jsr_n$$

The barrier V is determined by the lowest energy saddle point configuration determined by the stationarity condition $\delta\Delta E_N/\delta r_n = 0$. One can distinguish the string-like and single pancake regimes separated by the "decoupling" current $j_{\rm dec} = c\sqrt{\epsilon_1 U_0}/(\Phi_0 s)$. At $j < j_{\rm dec}$ the critical nucleus consists of $N > 1$ pancakes . The continuum limit corresponds to $N \gg 1$, i.e $j \ll j_{\rm dec}$ and one finds $N \simeq 2\sqrt{2}j_{\rm dec}/j >> 1$. The resulting string-like creep is characterized by a half loop width $w \approx cU_0/\Phi_0 j$ and the barrier $V_{\rm str}(j) \approx 4\sqrt{2}sU_0 j_{\rm dec}/(3j)$ and holds as long as $w < a$,d. Because of discreteness the number of the pancakes in the nucleus decreases by one with increase of the current at well defined transition currents $j = j_{N\to N-1}$, $j_{N\to N-1} = j_{\rm dec}\sqrt{2\sqrt{2}/N(N+1)}$. Thus for $j_{N+1\to N} < j < j_{N\to N-1}$, the barrier $V(j)$ is determined by the lowest energy for a N pancake excitation: $V(j) = E_N(j) = U_0\left(N - \frac{j^2}{24j_{\rm dec}^2}N(N+1)(N+2)\right)$. For $j \ll j$dec the last expression reduces to $V_{\rm str}$. Above $j_{\rm dec}$ pancakes liberate from the column independently with activation energy $\approx sU_0$.

We turn now to the collective localization of a pancake stack on the forest of columnar defects for $B < B_{cr} < B_\Phi$. There is a new "tight binding" regime for a localization of a single pancake stack by many columnar defects, which does not exist for continuous lines. Above the temperature $T_J \approx \epsilon_1 d^2/s$ pancakes can travel from column to column, but as long as $T < T^*$ one can neglect the probability to find pancakes outside the columns. There are two sources for weak localization on the forest of identical columns: fluctuation of column density and potential fluctuations due to superposition of individual long range column potentials. Here we focus on the density fluctuations which dominates at high temperatures, $T > s\epsilon_0 b_0/d$ and consider potential fluctuations elsewhere [11]. The localization length $\xi_l \gg d$ can be estimated as follows. When confining the pancake stack within the region of size ξ_l with enhanced number of columns $N = \bar{N} + \delta N$, $\bar{N} \approx (\xi_l/d)^2$ and $\delta N \sim \sqrt{\bar{N}}$, we gain the positional entropy due to the enhanced number of available states as $-(T/s)(\delta N/\bar{N}) \approx -(T/s)(d/\xi_l)$. The entropy loss due to suppression of pancake thermal wandering by columnar defects is $T^2/\epsilon_1\xi_l^2$. Optimizing the change in free energy $\delta F = -(T/s)(d/\xi_l) + T^2/\epsilon_1\xi_l^2$ we find the localization length and binding energy:

$$\xi_l \approx Ts/\epsilon_1 d;\ E_b \approx -\epsilon_1(d/s)^2. \quad (9)$$

It is important to note that in this regime the effectiveness of localization decreases with increase of column concentration due to the decrease of elemental jump distance.

The above results allow us to estimate the typical current, $j_{\rm dec} \approx cE_b/(\Phi_0\xi_l) \approx c\epsilon_1^2 d^3/(\Phi_0 s^3 T)$ at which the stack of pancake delocalizes from the weakly localized state. Note however that at $T < T^*$ the barriers controlling vortex hopping between columns of the are still large (of order of sU_0), and thus for $j > j_{\rm dec}$ the resistivity still remains much smaller than the flux flow resistivity ρ_{ff}: $\rho \approx \rho_{ff}\exp(-\frac{sU_0}{T})$. The resistivity approaches ρ_{ff} at much larger current $j_c = cU_0/(\Phi_0\xi)$. The current $j_{\rm dec}$ plays a role of "decoupling current" because at $j > j_{\rm dec}$ the interlayer coupling does not influence much the motion of pancakes.

At elevated temperature pancakes spend more time outside the columns and at $T = T^*$ there is a crossover from the "tight binding" regime to the gaussian random potential localization. In the latter regime vortices are localized by the gaussian fluctuations of the effective potential $\delta U_{eff} \approx -(T/s)\left[\exp\left(sU_0/T\right) - 1\right] b_0 r_0/(\xi_l d)$. Adding the confinement term $T^2/\epsilon_1\xi_l^2$ and optimizing leads to:

$$\xi_l = \frac{sTd}{\epsilon_1 b_0 r_0}(e^{\frac{sU_0}{T}} - 1)^{-1}; E_b = -\frac{\epsilon_1 b_0^2 r_0^2}{sd^2}(e^{\frac{sU_0}{T}} - 1)^2 \quad (10)$$

Eqs. (9,10) are valid at very small fields when intervortex interactions can be neglected. Interactions become relevant for $B > B_{cp} \approx \Phi_0 E_b/(\epsilon_0\xi_l^2)$ and lead to a collective pinning regime [11]. For the "tight binding" regime the crossover to collective pinning is expected at $B_{cp} \approx B_{cr}T_J^2/T^2$.

We now discuss the suppression of thermal decoupling by columnar defects. The effects of columns on the phase coherence between the layers is of a very different nature at high and low fields and have to be discussed separately. In the absence of columnar defects and at small fields $B < B_{cr} = \Phi_0/(\gamma s)^2$ the decoupling occurs in the

liquid phase when the mean square fluctuation, $u^2_{\rm neib} = \left\langle (r_{n+1} - r_n)^2 \right\rangle$, of the separations between the adjacent pancakes belonging to the same vortex line becomes of order a^2 [1]. For pin-free system $u^2_{\rm neib} = 2sT/\epsilon_1$ and $T_{\rm dec0}(B) \sim \epsilon_1 \Phi_0/2sB \sim T_m(B_{cr}/B)^{1/2} > T_m$ where T_m is the melting temperature of the pure system. Columnar defects suppress the tilt deformations of vortex lines and reduce their influence on the interlayer Josephson coupling. Since the vortex-vortex interactions have little effect on $u^2_{\rm neib}$ the above result for a single stack can be used. Correction to $u^2_{\rm neib}$ caused by columns is connected to binding energy by relation $\Delta u^2_{\rm neib} = 2s^2(\partial E_b/\partial \epsilon_1)$. For temperature range $T < T^*$ decoupling takes place within the "tight binding" regime. Using (9) we obtain $u^2_{\rm neib} \approx 2sT/\epsilon_1 - {\rm Const}\ d^2$ and the Lindemann-like criterion $u^2_{\rm neib} \approx a^2$ gives

$$T_{\rm dec} \approx T_{\rm dec0} + {\rm Const}\ \epsilon_1 d^2/s, \ {\rm at}\ T_{\rm dec} < T^* \qquad (11)$$

Note that in this regime the decoupling temperature *decreases* with the increase of the concentration of the columns due to decrease of the elemental jump distance. At $T_{\rm dec} > T^*$ one finds, similarly:

$$T_{\rm dec} \approx T_{\rm dec0} + \frac{sb_0^2 r_0^2}{d^2}\left[\exp\frac{sU_0}{T_{\rm dec0}} - 1\right]^2. \qquad (12)$$

As temperature approaches T_c, the renormalized decoupling line smoothly merges the unrenormalized one.

At large fields $B \gg B_\Phi, B_{cr}$ one has to take into account that (i) only a small fraction of vortices $\approx B/B_\Phi$ is trapped by columns, and (ii) the interaction between the vortex lattices in different layers is weaker than intralayer interactions. To estimate fluctuations of the phase difference between layers we note that the phase disturbance is $\delta\phi_n(\mathbf{q}) = 2\pi n_v u_{nt}/q_\perp$, where u_{nt} is the transverse component of the lattice displacement in the n-th layer at the wave vector $\mathbf{q}$. The resulting average phase difference between the layers $\left\langle(\Delta\phi)^2\right\rangle \equiv \langle(\delta\phi_n(\mathbf{r}) - \delta\phi_{n+1}(\mathbf{r}))^2\rangle$ is

$$\left\langle(\Delta\phi)^2\right\rangle = (2\pi n_v)^2 \int_{q_\perp > \pi/\gamma s} \frac{d\mathbf{q}_\perp}{(2\pi)^2} \frac{\langle|u_{nt}(q_\perp)|^2\rangle}{q_\perp^2}. \qquad (13)$$

The amplitude of the transverse vortex displacement can be estimated as $\langle|u_{nt}(q_\perp)|^2\rangle \approx T/(sC_{66}(q_\perp^2 + (\pi/d)^2))$, where $C_{66} = B\epsilon_0/4\Phi_0$ is the shear modulus. Performing integration we find $\left\langle(\Delta\phi)^2\right\rangle \approx TB/(s\epsilon_0 B_\Phi)\ln(\gamma s/d)$. Thus, the typical temperature $T_{\rm dec}$, above which the Josephson coupling is considerably suppressed can be estimated as

$$T_{\rm dec} \approx \frac{B_\Phi s\epsilon_0}{B\ln(\gamma s/d)}. \qquad (14)$$

The ratio of $T_{\rm dec}$ to the decoupling temperature for the ideal crystal $T_{\rm dec0}$ [1], $T_{\rm dec0} = (\Phi_0/4\pi B)^{1/2}\epsilon_0/\gamma$, is

$$T_{\rm dec}/T_{\rm dec0} \approx B_\Phi/\sqrt{B_{cr}B} \qquad (15)$$

Thus, at fields $B < B_\Phi^2/B_{cr}$ the columnar defects effectively increase the coupled region. For $B > B_\Phi^2/B_{cr}$ the curve $T_{\rm dec}$ smoothly merges with the decoupling line of the pure system. An important observation is that at large fields $T_{\rm dec}(B) < T_m$ and approaches T_m at $B \approx B_\Phi$. The vortex phase in the region $T_{\rm dec}(B) < T < T_m$ has infinite tilt modulus and therefore can be referred to as the "decoupled Bose glass". The largest upward shift of the decoupling temperature is expected to occur at $B \approx B_\Phi$ where the thermal motion of pancakes is maximally suppressed and pancakes do not travel from column to column.

To conclude, we have found three regimes of pancake localization on one column: low temperature, "pancake depinning", and "string depinning" regimes. A new "tight binding" regime of localization of a single pancake stack on many columns was found at high concentration of columns. We have studied the dynamic crossovers from line to pancake creep, which can be observed in transport experiments. We have shown that columnar defects "recouple" Josephson layers by suppression of pancake positional fluctuations. This effect can be checked in neutron diffraction and μSR experiments. We predict an upward shift of the decoupling line by columnar defects. A "decoupled Bose glass" phase is predicted at high field.

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[1] L.I.Glazman and A.E.Koshelev, Phys. Rev. B, **43**,2835 (1991), L.L.Daemen *et al* Phys.Rev.B **47** 11291 (1993)
[2] H.Pastoriza *et al*, Phys. Rev. Lett. **72**, 295 (1994); W.R.White *et al*, Phys. Rev .Lett. **66**, 2826 (1991), Phys. Rev. B**50** 6303
[3] W. Gerhäuser *et al*, Phys. Rev. Lett. **68**, 879 (1992).
[4] L. Civale *et al*, Phys. Rev. Lett. **67**, 648 (1991); M. Konczykowski*et al*, Phys. Rev. B 44, 7167 (1991);
[5] L. Klein *et al*, Phys. Rev. B **48** 3523 (1993).
[6] C. J. van der Beek *et al*, Phys. Rev. B **51**, 15492 (1995)
[7] M. Konczykowski *et al*, Phys. Rev. B, **51**, 3957 (1995)
[8] D.R.Nelson and V.M.Vinokur, Phys. Rev. Lett. **68**, 2398 (1992), Phys. Rev. B, **48**,13060 (1993)
[9] L. Krusin-Elbaum *et al*, Phys. Rev. Lett. **72**, 1914 (1994).
[10] G. S. Mkrtchyan and V. V. Shmidt, Sov. Phys. JETP 34, 195 (1972); A.Buzdin and D.Feinberg, Physica C**235-240**, 2755 (1994)
[11] A.E.Koshelev, P.Le Doussal, and V.M.Vinokur, unpub-

lished
[12] R. P. Feynman and A. R. Hibbs, *Quantum mechanics and path integrals*, NY, McGraw-Hill, 1965
[13] S.Ryu, A.Kapitulnik, and S.Doniach *et al*, Phys. Rev. Lett. **71**, 4245 (1993)
[14] J.Blatter *et al*, Rev. Mod. Phys., **66**, 1125, (1994)
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